



IXTP1N80 Information



For Reference Only

Part Number IXTP1N80 Manufacturer IXYS

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 800V 750MA TO-220AB

Package TO-220-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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IXTP1N80 Specifications

Manufacturer Part Number IXTP1N80 Manufacturer IXYS Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-220-3 Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 800V Current - Continuous Drain (Id) @ 25°C 750mA (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4.5V @ 25µA Gate Charge (Qg) (Max) @ Vgs 8.5nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 220pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 40W (Tc) Rds On (Max) @ Id, Vgs 11 Ohm @ 500mA, 10V Operating Temperature -55°C ~ 150°C (TJ)		
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Current - Continuous Drain (Id) @ 25°C 750mA (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4.5V @ 25μA Gate Charge (Qg) (Max) @ Vgs 8.5nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 220pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 40W (Tc) Rds On (Max) @ Id, Vgs 11 Ohm @ 500mA, 10V Operating Temperature -55°C ~ 150°C (TJ)	Technology	MOSFET (Metal Oxide)
$\begin{array}{llllllllllllllllllllllllllllllllllll$	Drain to Source Voltage (Vdss)	800V
Vgs(th) (Max) @ Id 4.5V @ 25μA Gate Charge (Qg) (Max) @ Vgs 8.5nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 220pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 40W (Tc) Rds On (Max) @ Id, Vgs 11 Ohm @ 500mA, 10V Operating Temperature -55°C ~ 150°C (TJ)	Current - Continuous Drain (Id) @ 25°C	750mA (Tc)
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Vgs (Max) ± 20 VFET Feature-Power Dissipation (Max) 40 W (Tc)Rds On (Max) @ Id, Vgs 11 Ohm @ 500 mA, 10 VOperating Temperature -55 °C ~ 150 °C (TJ)	Gate Charge (Qg) (Max) @ Vgs	8.5nC @ 10V
FET Feature - Power Dissipation (Max) 40W (Tc) Rds On (Max) @ Id, Vgs 11 Ohm @ 500mA, 10V Operating Temperature -55°C ~ 150°C (TJ)	Input Capacitance (Ciss) (Max) @ Vds	220pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 11 Ohm @ 500mA, 10V Operating Temperature -55°C ~ 150°C (TJ)	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs 11 Ohm @ 500mA, 10V Operating Temperature -55°C ~ 150°C (TJ)	FET Feature	-
Operating Temperature $-55^{\circ}\text{C} \sim 150^{\circ}\text{C} \text{ (TJ)}$	Power Dissipation (Max)	40W (Tc)
	Rds On (Max) @ Id, Vgs	11 Ohm @ 500mA, 10V
	Operating Temperature	-55°C ~ 150°C (TJ)
Mounting Type Through Hole	Mounting Type	Through Hole
Supplier Device Package TO-220AB	Supplier Device Package	TO-220AB
Package / Case TO-220-3	Package / Case	TO-220-3
Report errors?		Report errors?

IXTP1N80 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IXTP1N80 Payment Methods





















IXTP1N80 Shipping Methods













If you have any question about IXTP1N80, please do not hesitate to contact us!

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